1 Megabit

 $(128K \times 8)$

Erasable

CMOS

EPROM

UV

Low Voltage

Features

- Wide Power Supply Range, 3.0 V to 5.5 V
- Fast Read Access Time 120 ns
- Compatible with JEDEC Standard AT27C010
- Low Power 3.3-Volt CMOS Operation
 - 20 μA max. Standby
 - 29 mW max. Active at 5 MHz for V_{CC} = 3.6 V 138 mW max. Active at 5 MHz for Vcc = 5.5 V
- Wide Selection of JEDEC Standard Packages
 - 32-Lead 600-mil PDIP and Cerdip
 - 32-Pad PLCC and LCC
 - 32-Lead TSOP
- **High Reliability CMOS Technology** 2000 V ESD Protection
 - 200 mA Latchup Immunity
- Rapid Programming 100 µs/byte (typical)
- **Two-line Control**
- **CMOS and TTL Compatible Inputs and Outputs**
- Integrated Product Identification Code
- **Commercial and Industrial Temperature Ranges**

Description

The AT27LV010 chip is a low power, low voltage 1,048,576 bit ultraviolet erasable and electrically programmable read only memory (EPROM) organized as 128K x 8 bits. It requires only one supply in the range of 3.0 to 5.5 V in normal read mode operation, making it ideal for portable systems.

With a typical power draw of only 10 mW at 1 MHz and V_{CC} at 3.3 V, the AT27LV010 draws less than one-fifth the power of a standard 5-V EPROM. Standby mode supply current is typically less than 1 µA at 3.3 V. (continued)

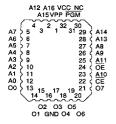
Pin Configurations

Pin Name	Function
A0-A16	Addresses
00-07	Outputs
CE	Chip Enable
ŌĒ	Output Enable
PGM	Program Strobe
NC	No Connect

CDIP, PDIP Top View

	_		- ·			
VPP	þ	1	\sim	32	Ь	vcc
A16	d	2		31	Þ	PGM
A15		3		30	Þ	NC
A12	d	3 4		30 29 28 27 26 25 24 23 22 21 20 19	Þ	A14
A7 A6	q	5		28	Þ	A13
A6	4	6		27	Þ	A8
A5 A4	q.	6 7		26	Þ	A9
A4	d.	8		25	Þ	A11
A3 A2 A1	Þ	9		24	Þ	OE A10 CE
A2	q	10		23	Þ	A10
A1	þ	11		22	Þ	CE
A0	d.	12		21	Þ	07
00	Þ	13		20	Þ	06
01	d	14		19	Þ	O5
O2 GND	0000000000	15		18 17		04
GND	d.	14 15 16		17	Þ	O3

LCC, PLCC Top View



TSOP Top View Type 1

A11 42 50 1 a	32 OE
A8 A9 5 3 2	30 31 B A10 CE
A14 A13 B 4 5	28 29 6 07 06
PGM NC 6 7	26 27 05 04
VCC P 8	25 ₽ 03
VPP A16 = 10 9	24 23 O2 GND
A15 A12 11 11	22 21 00 01
A7 A6 5 14 13	20 19 B A1 A0
A5 70 7 40 15	19 5 49
A4 🗆 16	10 17 5 A3 A2



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Description (Continued)

The AT27LV010 comes in a choice of industry standard JEDEC-approved packages, including: one-time programmable (OTP) plastic PDIP, PLCC, and TSOP, as well as windowed ceramic Cerdip and LCC. All devices feature two-line control $(\overline{CE}, \overline{OE})$ to give designers the flexibility to prevent bus contention.

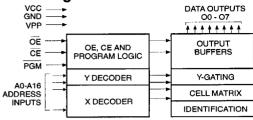
The AT27LV010 operating with V_{CC} at 3.0 V produces TTL level outputs that are compatible with standard TTL logic devices operating at $V_{CC} = 5.0 \text{ V}$.

Atmel's 27LV010 has additional features to ensure high quality and efficient production use. The Rapid Programming Algorithm reduces the time required to program the part and guarantees reliable programming. Programming time is typically only 100 μs /byte. The Integrated Product Identification Code electronically identifies the device and manufacturer. This feature is used by industry standard programming equipment to select the proper programming algorithms and voltages. The AT27LV010 programs identically as an AT27C010.

Erasure Characteristics

The entire memory array of the AT27LV010 is erased (all outputs read as VoH) after exposure to ultraviolet light at a wavelength of 2537 Å. Complete erasure is assured after a minimum of 20 minutes exposure using 12,000 µW/cm² intensity lamps spaced one inch away from the chip. Minimum erase time for lamps at other intensity ratings can be calculated from the minimum integrated erasure dose of 15 W-sec/cm². To prevent unintentional erasure, an opaque label is recommended to cover the clear window on any UV erasable EPROM which will be subjected to continuous fluorescent indoor lighting or sunlight.

Block Diagram



Absolute Maximum Ratings*

Temperature Under Bias40°C to +85°C
Storage Temperature65°C to +125°C
Voltage on Any Pin with Respect to Ground2.0 V to +7.0 V ⁽¹⁾
Voltage on A9 with Respect to Ground2.0 V to +14.0 V ⁽¹⁾
VPP Supply Voltage with Respect to Ground2.0 V to +14.0 V ⁽¹⁾
Integrated UV Erase Dose7258 W•sec/cm ²

*NOTICE: Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device.

This is a stress rating only and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of this specification is not implied.

Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

Notes:

Minimum voltage is -0.6 V dc which may undershoot to -2.0 V for pulses of less than 20 ns. Maximum output pin voltage is V_{CC} + 0.75 V dc which may be exceeded if certain precautions are observed (consult application notes) and which may overshoot to +7.0 V for pulses of less than 20 ns.

Operating Modes

Mode \ Pin	CE	ŌĒ	PGM	Ai	V_{PP}	Vcc	Outputs
Read	VIL	VIL	X ⁽¹⁾	Ai	Х	Vcc	Dout
Output Disable	Х	ViH	Х	X	Х	Vcc	High Z
Standby	ViH	Х	Х	X	X	Vcc	High Z
Rapid Program ⁽²⁾	VIL	ViH	VIL	Ai	VPP	Vcc (2)	DiN
PGM Verify ⁽²⁾	VIL	VIL	ViH	Ai	V _{PP}	Vcc (2)	Dout
PGM Inhibit ⁽²⁾	VıH	Х	Х	Х	V _{PP}	Vcc (2)	High Z
Product Identification ^{(2),(4)}	VIL	ViL	Х	A9=VH (3) A0=VIH or VIL A1-A16=VIL	X	Vcc (2)	Identification Code

Notes: 1. X can be V_{IL} or V_{IH}.

- Refer to Programming characteristics. Programming modes require V_{CC} ≥ 4.5 V.
- 3. $V_H = 12.0 \pm 0.5 \text{ V}$.

4. Two identifier bytes may be selected. All Ai inputs are held low (V_{IL}), except A9 which is set to V_H and A0 which is toggled low (V_{IL}) to select the Manufacturer's Identification byte and high (V_{IH}) to select the Device Code byte.

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AT27LV010 =

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D.C. and A.C. Operating Conditions for Read Operation

	AT27LV010						
	-12	-15	-20	-25			
Com.	0°C - 70°C	0°C - 70°C	0°C - 70°C	0°C - 70°C			
Ind.	-40°C - 85°C	-40°C - 85°C	-40°C - 85°C	-40°C - 85°C			
	3.0 V to 5.5 V	3.0 V to 5.5 V	3.0 V to 5.5 V	3.0 V to 5.5 V			
		Com. 0°C - 70°C Ind40°C - 85°C	-12 -15 Com. 0°C - 70°C 0°C - 70°C Ind. -40°C - 85°C -40°C - 85°C	-12 -15 -20 Com. 0°C - 70°C 0°C - 70°C 0°C - 70°C Ind. -40°C - 85°C -40°C - 85°C -40°C - 85°C			

= Advance Information

D.C. and Operating Characteristics for Read Operation

(VCC = 3.0 V to 5.5 V unless otherwise specified)

Symbol	Parameter	Condi	tion		Min	Max	Units
lц	Input Load Current	VIN = C	V to Vcc			±1	μΑ
lro	Output Leakage Current	Vout =	= 0 V to V _{CC}			±5	. μΑ
IPP1 (2)	V _{PP} ⁽¹⁾ Read/Standby Current	V _{PP} =	Vcc			10	μΑ
			1400\ 05 \ \ \ \ \ \ \ \ \ \ \ \ \ \ \ \ \ \ \	Vcc = 3	3.6 V	20	μА
laa.	V _{CC} ⁽¹⁾ Standby Current	ISB1 (C	CMOS), $\overline{CE} = V_{CC} \pm 0.3 \text{ V}$	Vcc = 5	5.5 V	100	μA
IsB	VCC V Standby Current		TIN OF ANN ASSA	Vcc = 3	3.6 V	100	μA
		Is _{B2} (TTL), $\overline{CE} = 2.0 \text{ to V}_{CC} + 0.5 \text{ V}$		Vcc = 5	5.5 V	1	mA
	Vcc Active Current		f = 5 MHz. louτ = 0 mA.	Com.		8	mA
		Icc ₁	CE = VIL, VCC = 3.6 V	Ind.		10	mA
lcc		lcc2	$\underline{f} = 5 \text{ MHz}, \text{ lout} = 0 \text{ mA}$ $\overline{\text{CE}} = \text{V}_{\text{IL}}, \text{ Vcc} = 5.5 \text{ V}$	Com.		25	mA
				Ind.		30	mA
V≀L	Input Low Voltage				-0.6	0.8	V
ViH	Input High Voltage				2.0	V _{CC} +0.5	V
.,	0 h	loL = 2	2.0 mA			.4	V
Vol	Output Low Voltage	loL = 1	00 μΑ			.2	٧
	0 1 11 1 1/1 1	Юн = -	2.0 mA		2.4		٧
Vон	Output High Voltage	Юн = -	100 μ A		Vcc-0.2	2	V

Notes: 1. V_{CC} must be applied simultaneously or before V_{PP} , and removed simultaneously or after V_{PP} .

2. Vpp may be connected directly to $V_{\rm CC}$, except during programming. The supply current would then be the sum of $I_{\rm CC}$ and $I_{\rm PP}$.

A.C. Characteristics for Read Operation (VCC = 3.0V to 5.5V)

				AT27LV010								
					12	-1	15	-2	20	-2	25	
Symbol	Parameter	Condition		Min	Max	Min	Max	Min	Max	Min	Мах	Units
tacc (3)	Address to Outrast Dalass	CE = OE = VIL	Com.		120		150		200		250	ns
TACC Y	Address to Output Delay	CE = CE = VIL	Ind.		120		150		200		250	ns
tcE (2)	CE to Output Delay	OE = VIL			120		150		200		250	ns
toE (2,3)	OE to Output Delay	CE = VIL			50		60		70		100	ns
t _{DF} (4,5)	OE or CE High to Output Float				40		50		50		50	ns
tон	Output Hold from Address, CE or OE, whichever occurred first			0		0		0		0		ns

Notes: 2, 3, 4, 5. - see AC Waveforms for Read Operation.

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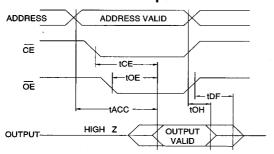




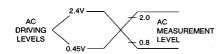
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A.C. Waveforms for Read Operation (1)



Input Test Waveform and Measurement Level



t_R, t_F < 20 ns (10% to 90%)

Notes:

- Timing measurement references are 0.8 V and 2.0 V. Input AC driving levels are 0.45 V and 2.4 V. See Input Test Waveforms and Measurement Levels.
- 2. \overline{OE} may be delayed up to t_{CE}-t_{OE} after the falling edge of \overline{CE} without impact on t_{CE}.
- OE may be delayed up to tACC-tOE after the address is valid without impact on tACC.
- This parameter is only sampled and is not 100% tested.
- Output float is defined as the point when data is no longer driven.

Output Test Load



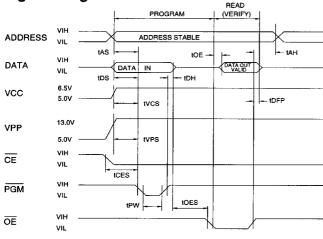
Note: C_L = 100 pF including jig capacitance.

Pin Capacitance (f = 1 MHz, $T = 25^{\circ}C$)

	Тур	Max	Units	Conditions	
CIN	4	8	pF	V _{IN} = 0 V	
Cout	8	12	pF	Vout = 0 V	

Notes: 1. Typical values for 5-V supply voltage. This parameter is only sampled and is not 100% tested.

Programming Waveforms (1)



Notes:

- 1. The Input Timing Reference is 0.8 V for V_{IL} and 2.0 V for V_{IH} .
- t_{OE} and t_{DFP} are characteristics of the device but must be accommodated by the programmer.
- When programming the AT27LV010 a 0.1-μF capacitor is required across V_{PP} and ground to suppress spurious voltage transients.

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D.C. Programming Characteristics

 $T_A = 25 \pm 5^{\circ}C$, $V_{CC} = 6.5 \pm 0.25 V$, $V_{PP} = 13.0 \pm 0.25 V$

Sym-		Test	Lir	nits	
bol	Parameter	Conditions	Min	Max	Units
ILI	Input Load Current	VIN=VIL,VIH		10	μΑ
VIL	Input Low Level	(All Inputs)	-0.6	0.8	٧
ViH	Input High Level		2.0	V _{CC+} 1	V
Vol	Output Low Volt.	I _{OL} =2.1 mA		.45	٧
Voн	Output High Volt.	Іон≕-400 μА	2.4		V
lcc2	V _{CC} Supply Curren (Program and Veri			40	mA
IPP2	V _{PP} Supply Current	CE=PGM=V _R		20	mA
VID	A9 Product Identification Voltage		11.5	12.5	V

A.C. Programming Characteristics

 $T_A = 25 \pm 5^{\circ}C$, $V_{CC} = 6.5 \pm 0.25 \text{ V}$, $V_{PP} = 13.0 \pm 0.25 \text{ V}$

_		Test			
Sym- bol	Parameter	Conditions* (see Note 1)	Lift Min	nits May 1	Units
DOI	Parameter	(300 14010 1)	IVIIII	IVIAX	Units
tas	Address Setup Tir	ne	2		μs
tces	CE Setup Time		2		μs
toes	OE Setup Time		2		μS
tos	Data Setup Time		2		μS
tan	Address Hold Tim	е	0		μs
tDH	Data Hold Time		2		μS
tDFP	OE High to Output Float Delay	(Note 2)	0	130	ns
tvps	V _{PP} Setup Time		2		μS
tvcs	V _{CC} Setup Time		2		μ\$
tpw	PGM Program Pulse Width	(Note 3)	95	105	μЅ
toE	Data Valid from O	Ē		150	ns

*A.C. Conditions of Test:

Input Rise and Fall Times (10% to 90%)	20 ns
Input Pulse Levels	. 0.45 V to 2.4 V $$
Input Timing Reference Level	0.8 V to 2.0 V
Output Timing Reference Level	0.8 V to 2.0 V

Notes:

- V_{CC} must be applied simultaneously or before V_{PP} and removed simultaneously or after V_{PP}.
- This parameter is only sampled and is not 100% tested.
 Output Float is defined as the point where data is no longer driven see timing diagram.
- 3. Program Pulse width tolerance is $100 \,\mu sec \pm 5\%$.

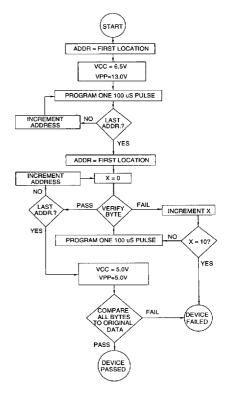
Atmel's 27LV010 Integrated Product Identification Code (1)

	Pins						Hex			
Codes	A0	07	O6	O 5	04	ОЗ	02	01	00	Data
Manufacturer	0	0	0	0	1	1	1	1	0	1E
Device Type	1	0	0	0	0	0	1	0	1	O5

Note: 1. The AT27LV010 has the same Product Identification Code as the AT27C010/L. Both are programming compatible.

Rapid Programming Algorithm

A 100 μs \overline{PGM} pulse width is used to program. The address is set to the first location. V_{CC} is raised to 6.5 V and Vpp is raised to 13.0 V. Each address is first programmed with one 100 μs \overline{PGM} pulse without verification. Then a verification/ reprogramming loop is executed for each address. In the event a byte fails to pass verification, up to 10 successive 100 μs pulses are applied with a verification after each pulse. If the byte fails to verify after 10 pulses have been applied, the part is considered failed. After the byte verifies properly, the next address is selected until all have been checked. Vpp is then lowered to 5.0 V and V_{CC} to 5.0 V. All bytes are read again and compared with the original data to determine if the device passes or fails.





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Ordering Information

tacc (ns) lcc (mA) Vcc = 3.6 V Active Standby		= 3.6 V	Ordering Code	Package	Operation Range		
120	8	0,02	AT27LV010-12DG AT27LV010-12JG AT27LV010-12LG AT27LV010-12PG AT27LV010-12TG	32DW6 32J 32LW 32P6 32T	Commercial (0°C to 70°C)		
120	10	0.02	AT27LV010-12DI AT27LV010-12JI AT27LV010-12LI AT27LV010-12PI AT27LV010-12TI	32DW6 32J 32LW 32P6 32T	Industrial (-40°C to 85°C)		
150	8	0.02	AT27LV010-15DC AT27LV010-15JC AT27LV010-15LC AT27LV010-15PC AT27LV010-15TC	32DW6 32J 32LW 32P6 32T	Commercial (0°C to 70°C)		
150	10	0.02	AT27LV010-15DI AT27LV010-15JI AT27LV010-15LI AT27LV010-15PI AT27LV010-15TI	32DW6 32J 32LW 32P6 32T	Industrial (-40°C to 85°C)		
200	8	0.02	AT27LV010-20DC AT27LV010-20JC AT27LV010-20LC AT27LV010-20PC AT27LV010-20TC	32DW6 32J 32LW 32P6 32T	Commercial (0°C to 70°C)		
200	10	0.02	AT27LV010-20DI AT27LV010-20JI AT27LV010-20LI AT27LV010-20PI AT27LV010-20TI	32DW6 32J 32LW 32P6 32T	Industrial (-40°C to 85°C)		
250	8	0.02	AT27LV010-25DC AT27LV010-25JC AT27LV010-25LC AT27LV010-25PC AT27LV010-25TC	32DW6 32J 32LW 32P6 32T	Commercial (0°C to 70°C)		
250	10	0.02	AT27LV010-25DI AT27LV010-25JI AT27LV010-25LI AT27LV010-25PI AT27LV010-25TI	32DW6 32J 32LW 32P6 32T	Industrial (-40°C to 85°C)		

= Advance Information

AT27LV010

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Ordering Information

	Package Type			
32DW6	32 Lead, 0.600" Wide, Windowed, Ceramic Dual Inline Package (Cerdip)			
32J	32 Lead, Plastic J-Leaded Chip Carrier OTP (PLCC)			
32LW	32 Pad, Windowed, Ceramic Leadless Chip Carrier (LCC)			
32P6	32 Lead, 0.600" Wide, Plastic Dual Inline Package OTP (PDIP)			
32T	32 Lead, Plastic Thin Small Outline Package OTP (TSOP)			

